

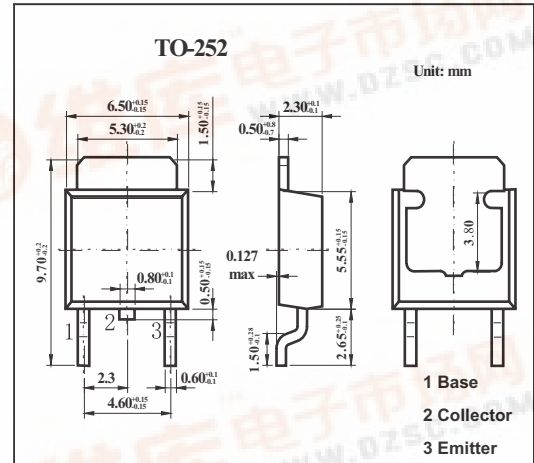
SMD Type Transistors

PNP Epitaxial Silicon Transistor

MJD350

Features

- Load Formed for Surface Mount Application
- Straight Lead



Absolute Maximum Ratings Ta = 25°C unless otherwise noted

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-300	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-300	V
Emitter-Base Voltage	V <sub>EBO</sub>	-3	V
Collector Current (DC)	I <sub>C</sub>	-0.5	A
Collector Current (Pulse)	I <sub>CP</sub>	-0.75	A
Collector Dissipation (TC = 25°C)	P <sub>C</sub>	15	A
Collector Dissipation (Ta = 25°C)		1.56	W
Junction Temperature	T <sub>J</sub>	150	W
Storage Temperature	T <sub>STG</sub>	-65 to 150	°C

Electrical Characteristics Ta = 25°C unless otherwise noted

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-Emitter Sustaining Voltage *	V <sub>CEO(sus)</sub>	I <sub>C</sub> = 1mA, I <sub>B</sub> = 0	-300			V
Collector Cut-off Current	I <sub>CEO</sub>	V <sub>CB</sub> = -300V, I <sub>E</sub> = 0			-0.1	mA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> = -3V, I <sub>C</sub> = 0			-0.1	mA
DC Current Gain *	h <sub>FE</sub>	V <sub>CE</sub> = -10V, I <sub>C</sub> = -50mA	30		240	

\*Pulse Test: PW ≤ 300μs, Duty Cycle ≤ 2%

